

3 A Schottky Barrier Rectifier

DESCRIPTION

In Microsemi's new Powermite3[®] SMT package, these high efficiency ultrafast rectifiers offer the power handing capabilities previously found only in much larger packages. They are ideal for SMD applications that operate at high frequencies.

In addition to its size advantages, Powermite3[®] package features include a full metallic bottom that eliminates the possibility of solder flux entrapment during assembly, and a unique locking tab acts as an integral heat sink. Its innovative design makes this device ideal for use with

automatic insertion equipment.

IMPORTANT: For the most current data, consult MICROSEMI's website: http://www.microsemi.com

ABSOLUTE MAXIMUM RATINGS AT 25° C (UNLESS OTHERWISE SPECIFIED)					
Rating	Symbol	Value	Unit		
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V _{RRM} V _{RWM} V _R	60	v		
RMS Reverse Voltage	V _{R (RMS)}	42	V		
Average Rectified Output Current	lo	3	А		
Non-Repetitive Peak Forward Surge Current 8.3ms Single half sine wave Superimposed on Rated Load	I _{FSM}	100 @ 25 °C 50 @ 100 °C	A		
Storage Temperature	T stg	-55 to +150	°C		
Operating Temperature	Т ор	-55 to +125	°C		

THERMAL CHARACTERISTICS (UNLESS OTHERWISE SPECIFIED)

Thermal Resistance			
Junction-to Bottom	Rja (1)	2.5	°C/Watt

(1) When Mounted on PC board with 2 ounce copper pattern.

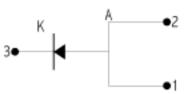


KEY FEATURES

- High power surface mount package.
- Guard Ring die construction for transient protection.
- Silicon Schottky rectifiers no reverse voltage recovery.
- Internal heat sink locking tabs
- Low forward voltage.
- Full metallic bottom eliminates flux entrapment
- Compatible with automatic insertion equipment
- Low profile-maximum height of 1mm supplied in 16 mm tape reel- 5000 units/ 13" reel.

APPLICATIONS/BENEFITS

- Switching and Regulating Power Supplies.
- Charge Pump Circuits.
- Reduces reverse recovery loss due to low I_{RM}.
 - Small foot print 190 X 300 mils 1:1 Actual size



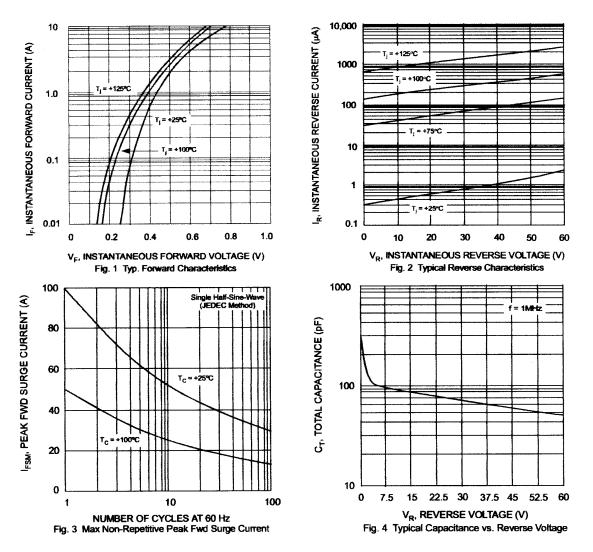
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Parameter	Symbol	Conditions	Min	Тур.	Max	Unit
Forward Voltage (Note 1)		I _F = 3.5 A , T _i =25 °C		0.59	0.63	
	V_{Fm}	$I_F = 3.5 \text{ A}, T_j = 125 \text{ °C}$ $I_F = 7 \text{ A}, T_j = 25 \text{ °C}$ $I_F = 7 \text{ A}, T_j = 25 \text{ °C}$ $I_F = 7 \text{ A}, T_j = 25 \text{ °C}$		0.53 0.72 0.63	0.57 0.76 0.67	V
Reverse Break Down Voltage Note 1)	V _{BR}	I _R = 0.2 mA	60			V
Reverse Current (Note1)	Im			2 0.6 2.5	200 20 150	μA mA mA
Capacitance	CT	$V_{R} = 4 V; F = 1 MH_{Z}$		130		pF

Note: 1 Short duration test pulse used to minimize self - heating effect.

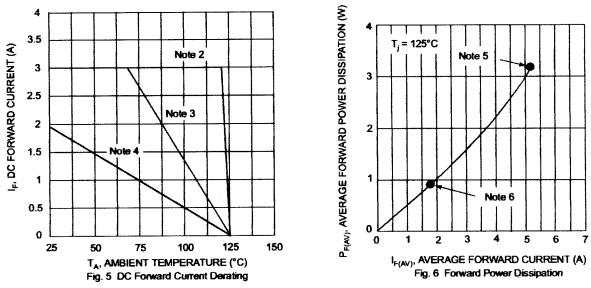


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ELECTRICALS



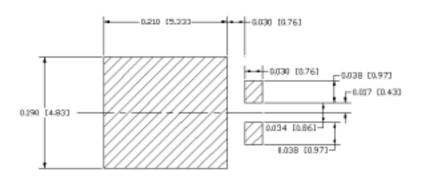
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Notes:

- 2. $T_A = T_{SOLDERING POINT}$, $R_{0JS} = 3.2^{\circ}C/W$, $R_{0SA} = 0^{\circ}C/W$.
 - 3. Device mounted on GETEK substrate, 2"x2", 2 oz. copper, double-sided, cathode pad dimensions 0.75" x 1.0", anode pad
 - dimensions 0.25" x 1.0". R_{tula} in range of 20-40°C/W. 4. Device mounted on FR-4 substrate, 2"x2", 2 oz. copper, single-sided, pad layout as per Diodes Inc. suggested pad layout document AP02001 which can be found on our website at http://www.diodes.com/datasheets/ap02001.pdf. RoJA in range of 100-120°C/W.
 - 5. Maximum power dissipation when the device is mounted in accordance to the conditions described in Note 3.
 - 6. Maximum power dissipation when the device is mounted in accordance to the conditions described in Note 4.

PAD LAYOUT



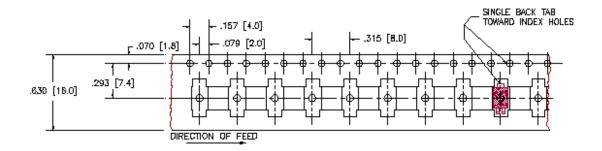
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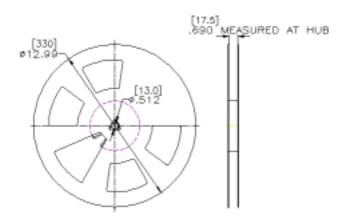


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13 INCH REEL





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